

isc Silicon PNP Power Transistor

2SA1964

DESCRIPTION

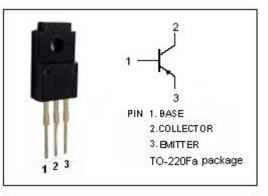
- Collector-Emitter Breakdown Voltage-
 - : V_{(BR)CEO}= -160V(Min)
- Good Linearity of h_{FE}
- Wide Area of Safe Operation
- Complement to Type 2SC5248
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

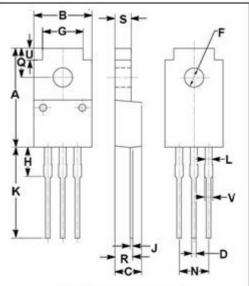
APPLICATIONS

- Power amplifier applications.
- Driver stage amplifier applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|--|-------|------|
| V _{CBO} | Collector-Base Voltage | -160 | V |
| V _{CEO} | Collector-Emitter Voltage | -160 | V |
| V _{EBO} | Emitter-Base Voltage | -5 | V |
| Ι _C | Collector Current-Continuous | -1.5 | A |
| | Collector Power Dissipation @T _a =25°C | 2 | 10/ |
| Pc | Collector Power Dissipation @T _c =25℃ | 20 | W |
| TJ | Junction Temperature 150 | | °C |
| T _{stg} | tg Storage Temperature -5 | | °C |





| | m | m |
|-----|-------|-------|
| DIM | MIN | MAX |
| Α | 16.85 | 17.15 |
| В | 9.54 | 10.10 |
| С | 4.35 | 4.65 |
| D | 0.75 | 0.90 |
| F | 3.20 | 3.40 |
| G | 6.90 | 7.20 |
| H | 3.80 | 4.20 |
| J | 0.45 | 0.75 |
| Κ | 13.35 | 13.80 |
| L | 1.10 | 1.30 |
| Ν | 4.98 | 5.18 |
| Q | 4.85 | 5.15 |
| R | 2.55 | 3.25 |
| S | 2.70 | 2.90 |
| U | 1.75 | 2.05 |
| V | 1.30 | 1.50 |

isc website: www.iscsemi.com

isc & iscsemi is registered trademark



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ELECTRICAL CHARACTERISTICS

Tj=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | МАХ | UNIT |
|----------------------|--------------------------------------|---|------|------|------|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = -1mA; I _B = 0 | -160 | | | V |
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | I _C = -50 μ A; I _E = 0 | -160 | | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E = -50 μ A; I _C = 0 | -5 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = -1A; I _B = -0.1A | | | -1.0 | V |
| Ісво | Collector Cutoff Current | V _{CB} = -160V; I _E = 0 | | | -1.0 | μA |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = -4V; I _C = 0 | | | -1.0 | μA |
| h _{FE} | DC Current Gain | Ic= -0.1A; Vce= -5V | 60 | | 200 | |
| fT | Current-Gain—Bandwidth Product | Ic= -0.2A; VcE= -10V | | 150 | | MHz |
| Сов | Output Capacitance | I _E = 0; V _{CB} = -10V; f= 1MHz | | 35 | | pF |

h_{FE} Classifications

| D | Е |
|--------|---------|
| 60-120 | 100-200 |

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